

Vishay Siliconix

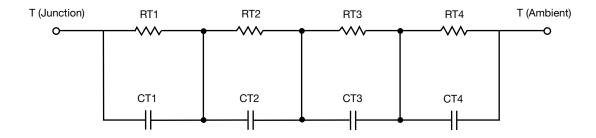
R-C Thermal Model Parameters

DESCRIPTION

The parametric values in the R-C thermal model have been derived using curve-fitting techniques. R-C values for the electrical circuit in the Foster/tank and Cauer/filter configurations are included. When implemented in P-SPICE, these values have matching characteristic curves to the single-pulse transient thermal impedance curves for the MOSFET.

These RC values can be used in the P-SPICE simulation to evaluate the thermal behavior of the MOSFET junction temperature under a defined power profile. These techniques are described in application note AN609, "Thermal Simulation of Power MOSFETs on the P-SPICE Platform".

R-C THERMAL MODEL FOR TANK CONFIGURATION



THERMAL RESISTANCE (°C/W)					
Junction to	Ambient	Case	Foot		
RT1	N/A	58.6896m	N/A		
RT2	N/A	161.2852m	N/A		
RT3	N/A	200.5605m	N/A		
RT4	N/A	280.9686m	N/A		
	THERMAL CAPAC	ITANCE (Joules/°C)			
Junction to	Ambient	Case	Foot		
CT1	N/A	1.7085m	N/A		
CT2	N/A	166.6650m	N/A		
CT3	N/A	136.2328m	N/A		
CT4	N/A	11.7993m	N/A		

Note

• n/a indicates not applicable

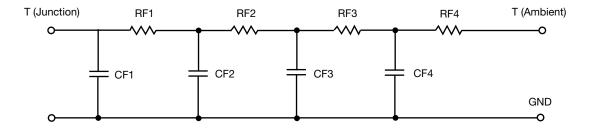
This document is intended as a SPICE modeling guideline and does not constitute a commercial product datasheet. Designers should refer to the appropriate datasheet of the same number for guaranteed specification limits.

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R-C THERMAL MODEL FOR FILTER CONFIGURATION



THERMAL RESISTANCE (°C/W)					
Junction to	Ambient	Case	Foot		
RF1	N/A	91.9523m	N/A		
RF2	N/A	326.5295m	N/A		
RF3	N/A	21.0228m	N/A		
RF4	N/A	260.4954m	N/A		
	THERMAL CAPAC	ITANCE (Joules/°C)			
Junction to	Ambient	Case	Foot		
CF1	N/A	1.4271m	N/A		
CF2	N/A	9.8289m	N/A		
CF3	N/A	66.8502m	N/A		
CF4	N/A	10.6678m	N/A		

Note

• n/a indicates not applicable





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